

MDL-NS-808/1~100mW



**NANOSECOND PULSED
INFRARED DIODE LASER
AT 808nm**

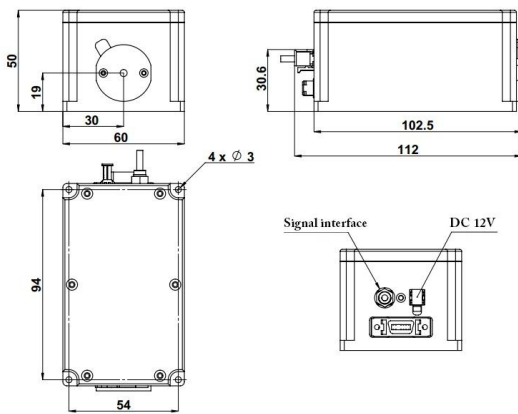
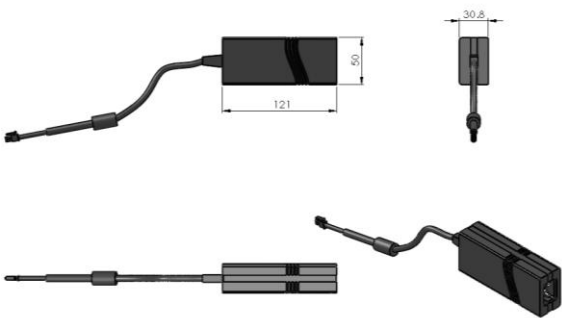
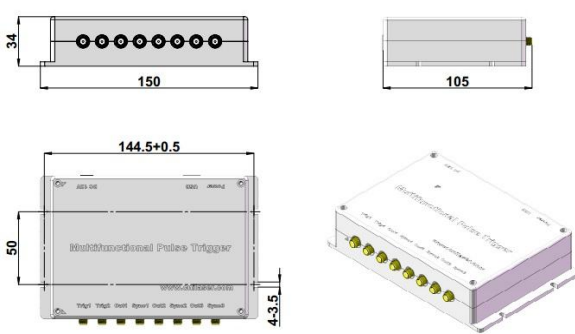
This series laser products with excellent material removal rate, are widely used in microelectronics, material processing, solar energy and medical equipment manufacturing, etc.



SPECIFICATIONS

Central wavelength (nm)	808±3
Output power@3.3VDC (mW, CW)	>1, 10, 20, ...,100
Pulse width (FWHM)	>10ns, 20ns, ...,10ms
Transverse mode	Near TEM ₀₀
Noise of amplitude(rms, CW)	<1%
M ² factor	<1.5
Beam diameter at the aperture (1/e ² ,mm)	~3.5
Beam divergence, full angle (mrad)	<1.0
User trigger frequency (Multifunctional Pulse Trigger optional)	1Hz-40MHz (1Hz-25MHz by using CNI Multifunctional Pulse Trigger)
Rise Time (ns)	<3
Fall Time (ns)	<3
Modulation Depth (extinction ratio)	>1000000:1
Warm-up time (minutes)	<5
Beam height from base plate (mm)	19
Operating temperature (°C)	10~35
Input voltage	+12VDC
Expected lifetime (hours)	10000
Warranty	1 year



MDL-NS-808	Optional Power Supply	Multifunctional Pulse Trigger
 <p>112(L) ×60(W) ×50(H) mm³, 0.5kg</p>	 <p>121(L) ×50(W) ×30.8(H) mm³, 0.3kg</p>	 <p>150(L) ×105(W) ×34(H) mm³, 0.5kg</p>